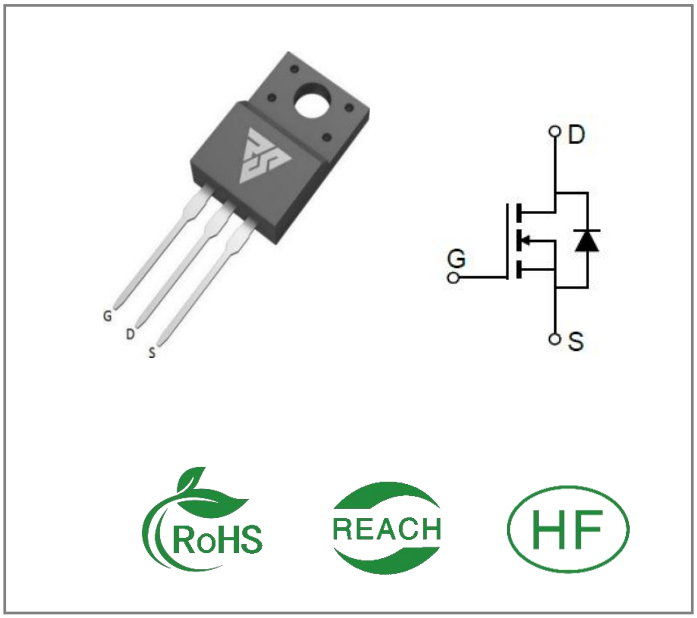
VDS	RDS(on)Typ	ID@25℃
800V	380mΩ	10A



Applications:

- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications

Features:

- Wide Bandgap SiC MOSFET Technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Low Reverse Recovery (Qrr)
- Easy to Parallel and Simple to Drive
- Robust against Parasitic Turn on Even 0V Turn off Gate Voltage

Benefits:

- Reduced Switching Losses
- Increased System Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements
- Reduced EMI

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSM080380F	TO-220F	RSM080380F	Tube	50 PCS

Maximum Ratings (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
VDS	Drain - Source Voltage	800	V	VGS=0V,ID=500μA
VGS	Gate - Source Voltage	-10/+22	V	Absolute maximum values
VGSOP	Recommended Operation Voltage of Gate to Source	0/+18	V	Recommended operational values
ID	Continuous Drain Current	10	A	VGS=15V, TC =25℃
IDM	Pulsed Drain Current	22	A	VGS=15V, TC =25℃
EAS	Single Pulsed Avalanche Energy	45	mJ	VDD=50V,L=10mH,IAS=3A
PD	Power Dissipation	24	W	TC =25℃, TJ =175℃
TJ, Tstg	Operating Junction and StorageTemperature	-55 to + 175	℃	

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Electrical Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V(BR)DSS	Drain-Source Breakdown Voltage	800			V	VGS=0V,ID=500μA	
VGS(th)	Gate Threshold Voltage	2.5	3.2	4.5	V	VGS= VDS, ID=1.8mA	
IDSS	Zero Gate Voltage Drain Current			10	μA	VDS=800V, VGS=0V	
IGSS	Gate-Source Leakage Current			250	nA	VGS=18V, VDS=0V	
RDS(on)	Drain-Source on-state Resistance		380	480	mΩ	VGS=15V, ID =10A	
			280	400		VGS=18V, ID =10A	
Ciss	Input Capacitance		254		pF	VGS=0V, VDS=500V f=1MHz,Tj=25℃	
Coss	Output Capacitance		20.2				
Crss	Reverse Transfer Capacitance		2.4				
RG	Gate Resistance		14.3		Ω	f=1 MHz, VAC=25mV	
Qg	Total Gate Charge		21.3		nC	VDS=500V VGS=0/+15V ID=5A	
Qgs	Gate to Source Charge		6.7				
Qgd	Gate to Drain Charge		11.5				
td(on)	Turn-On Delay Time		24		ns	VDD=500V VGS =0/15V ID=5A RG(ext)=10Ω	
tr	Rise Time		42				
td(off)	Turn-Off Delay Time		26.8				
tf	Fall Time		76				

Reverse Diode Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Max	Unit	Test Conditions	Note
VSD	Diode Forward Voltage	3.5		V	VGS=0V, ISD =3A	
IS	Continuous Diode Forward Current		10	A	VGS=0V,Tj= 25℃	
trr	Reverse Recovery time	17.8		ns	VGS=0V,ISD=5A VR=500V,Tj=25℃ di/dt=530A/us	
Qrr	Reverse Recovery Charge	33.7		nC		
Irrm	Peak Reverse Recovery Current	3.5		A		

Thermal Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions
RθJC	Thermal Resistance from Junction to Case	6.25		℃/W	

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Typical Feature Curve

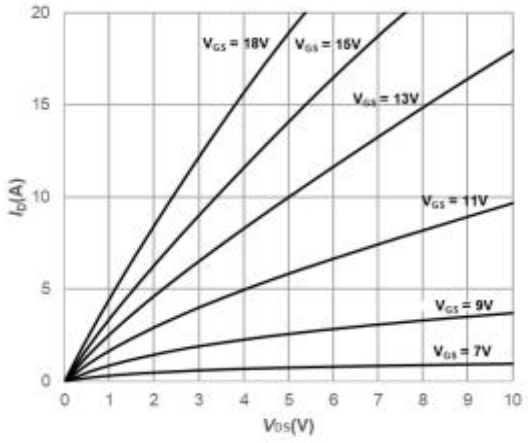

Fig1. Output Characteristics T_j=25℃

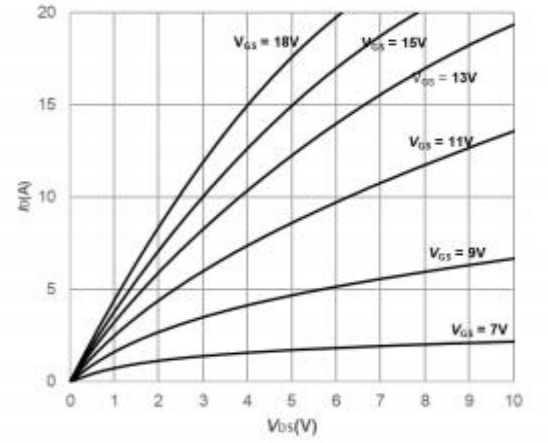

Fig2. Output Characteristics T_j=175℃

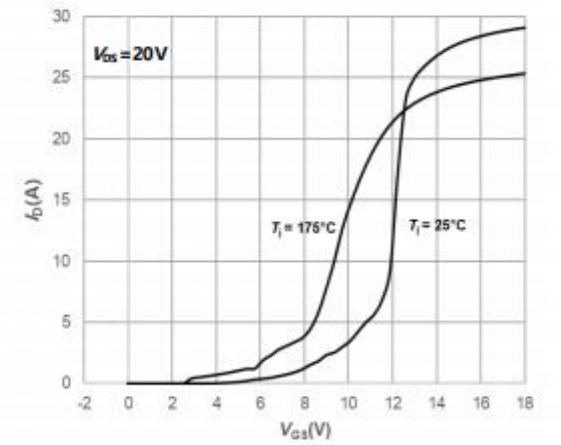

Fig3. Typical Transfer Characteristics

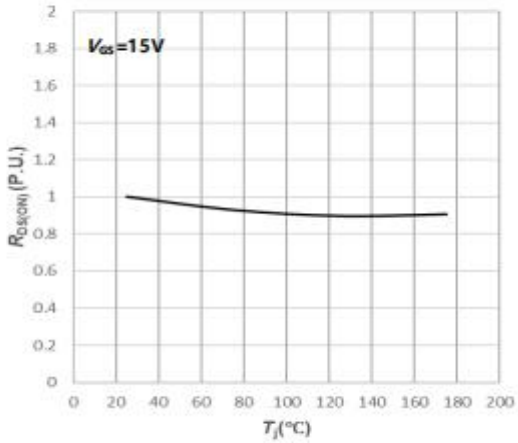

Fig4. Normalized On-Resistance vs. Temperature

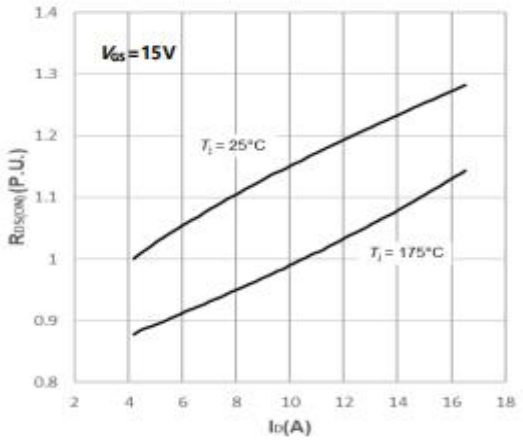

Fig5. Normalized On-Resistance vs. Drain Current For Various Temperatures

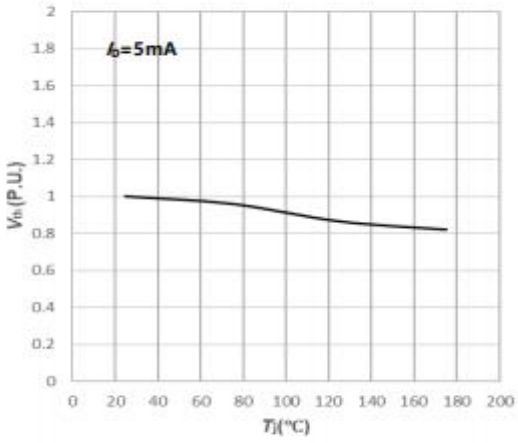

Fig6. Normalized Threshold Voltage vs. Temperature

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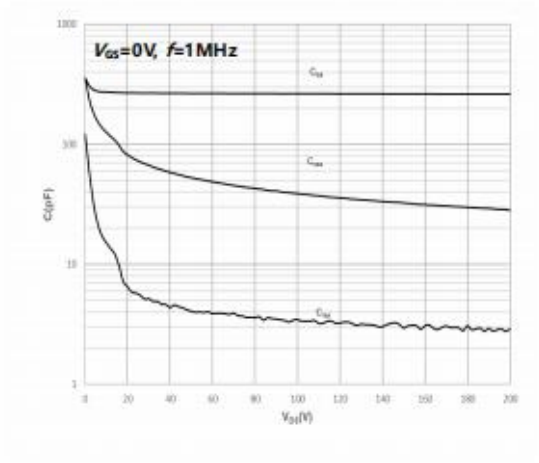

Fig7. Capacitances vs. Drain-Source Voltage (0-200V)

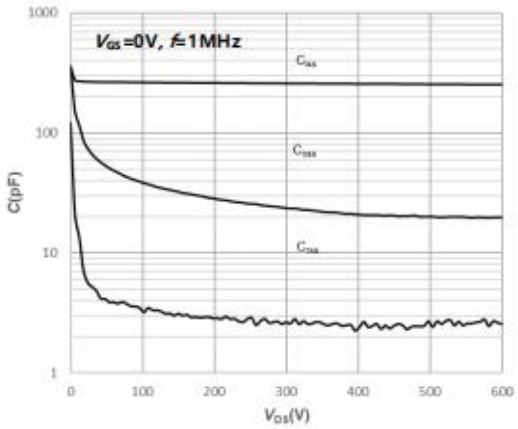

Fig8. Capacitances vs. Drain-Source Voltage (0-600V)

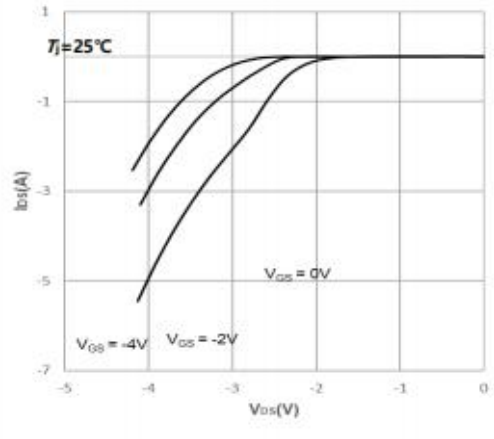

Fig9. Body Diode Characteristics

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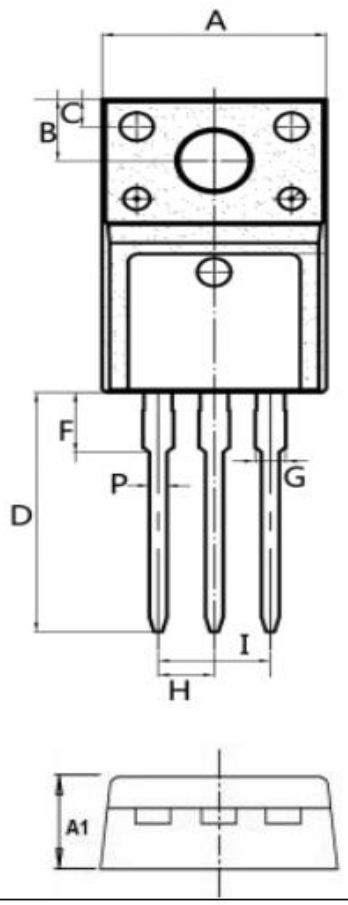
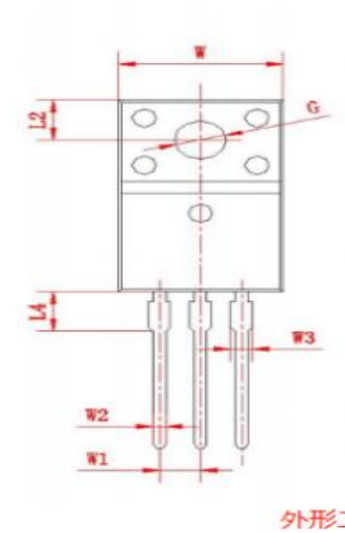
Package outline drawing(TO-220F Unit: mm)



外形一

Dim.	Min.	Max.
A	9.95	10.36
A1	4.5	5.0
B	2.95	3.25
C	1.25	1.45
D	12.60	13.60
E	0.40	0.60
F	2.8	3.5
G	1.30	1.45
H	(2.54)	
I	(5.08)	
J	4.60	4.75
K	2.45	2.65
L	6.5	6.8
M	15.4	16.0
N	2.25	3.05
O	0.45	0.55
P	0.70	0.90
All Dimensions in millimeter		



外形二

Dim.	Min.	Max.
W	9.95	10.36
W1	(2.54)	
W2	0.70	0.90
W3	1.25	1.47
L	15.67	16.07
L1	6.48	6.88
L2	3.2	3.4
L3	12.6	13.6
L4	(3.23)	
T	4.50	4.90
T1	2.34	2.74
T2	2.25	2.95
T3	0.45	0.60
T4	(0.70)	
G	3.08	3.28
All Dimensions in millimeter		

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